

Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10/600,598 on March 09, 2004

Combined Classifications

18 257/E21.584	2 257/E21.256
14 438/637	2 257/E21.309
14 438/687	2 257/E21.588
11 257/E21.585	2 257/E23.167
9 257/E23.145	2 427/123
9 438/627	2 427/304
9 438/638	2 427/96
8 257/E21.582	2 438/612
7 257/758	2 438/666
7 438/622	2 438/675
7 438/629	2 438/678
7 438/643	2 438/688
6 257/774	2 438/689
6 257/E21.576	2 438/692
6 438/624	2 438/745
6 438/633	2 438/775
6 438/672	
5 257/751	
5 257/762	
5 438/618	
5 438/628	
5 438/653	
4 438/644	
4 438/648	
3 204/192.25	
3 257/752	
3 257/760	
3 257/763	
3 257/E21.508	
3 257/E21.579	
3 257/E21.583	
3 257/E21.586	
3 257/E21.589	
3 257/E23.02	
3 427/97	
3 438/625	
3 438/634	
3 438/639	
3 438/656	
3 438/660	
3 438/685	
2 204/192.15	
2 204/192.22	
2 204/192.23	
2 204/298.07	
2 204/298.11	
2 257/622	
2 257/741	
2 257/761	
2 257/764	
2 257/773	
2 257/E21.251	

- 14 438/637 (1 OR, 13 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL -  
438/597 .To form ohmic contact to semiconductive material  
438/618 ..Contacting multiple semiconductive regions (i.e., interconnects)  
438/622 ...Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)  
438/637 ....With formation of opening (i.e., viahole) in insulative layer
- 14 438/687 (6 OR, 8 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive material  
438/687 ..Copper or copper alloy conductor
- 9 438/627 (0 OR, 9 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive material  
438/618 ..Contacting multiple semiconductive regions (i.e., interconnects)  
438/622 ...Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)  
438/625 ....At least one metallization level formed of diverse conductive layers  
438/627 .....At least one layer forms a diffusion barrier
- 9 438/638 (3 OR, 6 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive material  
438/618 ..Contacting multiple semiconductive regions (i.e., interconnects)  
438/622 ...Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)  
438/637 ....With formation of opening (i.e., viahole) in insulative layer  
438/638 .....Having viaholes of diverse width

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~~7 257/758 (2 OR, 5 XR)~~  
Class 257 : ACTIVE SOLID-STATE DEVICES

257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
257/741 .Of specified material other than unalloyed  
aluminum  
257/750 ..Layered  
257/758 ...Multiple metal levels on semiconductor,  
separated by insulating layer (e.g., multiple level  
metallization for integrated circuit)

7 438/622 (2 OR, 5 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive  
material  
438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)  
438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)

7 438/629 (1 OR, 6 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive  
material  
438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)  
438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)  
438/625 ....At least one metallization level formed of  
diverse conductive layers  
438/629 .....Diverse conductive layers limited to  
viahole/plug

7 438/643 (2 OR, 5 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive  
material  
438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)  
438/642 ...Diverse conductors  
438/643 ....At least one layer forms a diffusion  
barrier

6 257/774 (3 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
257/773 .Of specified configuration  
257/774 ..Via (interconnection hole) shape

6 438/624 (0 OR, 6 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL

438/597 .To form ohmic contact to semiconductive  
material

438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)

438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)

438/624 ....Separating insulating layer is laminate or  
composite of plural insulating materials

6 438/633 (1 OR, 5 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL

438/597 .To form ohmic contact to semiconductive  
material

438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)

438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)

438/631 ....Having planarization step

438/633 .....Simultaneously by chemical and mechanical  
means

6 438/672 (0 OR, 6 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL

438/597 .To form ohmic contact to semiconductive  
material

438/669 ..And patterning of conductive layer

438/672 ...Plug formation (i.e., in viahole)

5 257/751 (1 OR, 4 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
257/741 .Of specified material other than unalloyed  
aluminum  
257/750 ..Layered  
257/751 ...At least one layer forms a diffusion barrier

5 257/762 (1 OR, 4 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
257/741 .Of specified material other than unalloyed  
aluminum  
257/750 ..Layered  
257/762 ...At least one layer containing silver or  
copper

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- 5 438/618 (2 OR, 3 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL
- 438/597 .To form ohmic contact to semiconductive  
material
- 438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)
- 5 438/628 (1 OR, 4 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL
- 438/597 .To form ohmic contact to semiconductive  
material
- 438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)
- 438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)
- 438/625 ....At least one metallization level formed of  
diverse conductive layers
- 438/628 .....Having adhesion promoting layer
- 5 438/653 (0 OR, 5 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL
- 438/597 .To form ohmic contact to semiconductive  
material
- 438/652 ..Plural layered electrode or conductor
- 438/653 ...At least one layer forms a diffusion barrier
- 4 438/644 (0 OR, 4 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL
- 438/597 .To form ohmic contact to semiconductive  
material
- 438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)
- 438/642 ...Diverse conductors
- 438/644 ....Having adhesion promoting layer
- 4 438/648 (0 OR, 4 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL
- 438/597 .To form ohmic contact to semiconductive  
material

PLUS Search Results for S/N 10/600,598, Searched March 09, 2004 (Top 50)

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

5904565	5677244	6046108	6204179	6352921
6023102	5948705	6048790	6205658	6380065
6037250	6096648	6059940	6207222	6399486
6191023	6146517	6059940	6255192	6406939
6040240	5243222	6077779	6261952	6410435
6133144	5897369	6146988	6274923	6410442
6350667	5939788	6180523	6278153	6417575
6492735	5939334	6181013	6281589	6424044
6607978	5989623	6197681	6329701	6429119
4410622	6004188	6204168	6348408	6448654